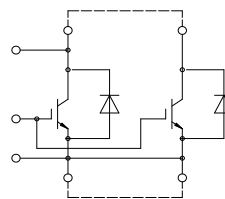
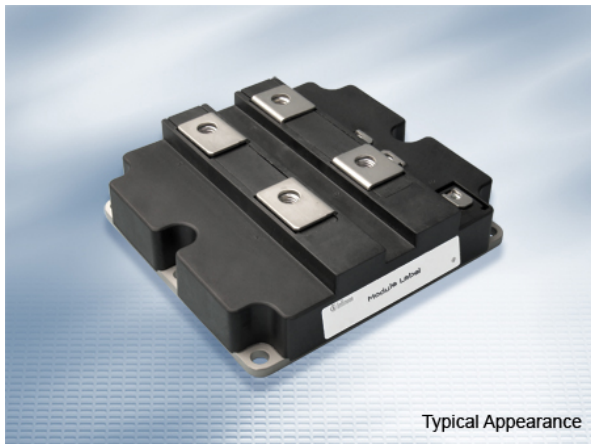


IHM-B 模块 采用第三代高速沟槽栅/场终止IGBT和第三代发射极控制二极管
IHM-B module with fast Trench/Fieldstop IGBT3 and Emitter Controlled 3 diode



external connection
(to be done)

$V_{CES} = 3300V$
 $I_{C\ nom} = 1000A / I_{CRM} = 2000A$

潜在应用

- UPS系统
- 中压变流器
- 斩波应用
- 牵引变流器
- 电机传动
- 风力发电机

电气特性

- $T_{vj\ op} = 150^{\circ}C$
- V_{CESat} 带正温度系数
- 低 V_{CESat}
- 低开关损耗
- 无与伦比的坚固性
- 高直流电压稳定性
- 高短路能力

机械特性

- IHM B 封装
- 封装的 CTI > 600
- 碳化硅铝 (AlSiC) 基板提供更高的温度循环能力
- 绝缘的基板

Potential Applications

- UPS systems
- Medium voltage converters
- Chopper applications
- Traction drives
- Motor drives
- Wind turbines

Electrical Features

- $T_{vj\ op} = 150^{\circ}C$
- V_{CESat} with positive temperature coefficient
- Low V_{CESat}
- Low switching losses
- Unbeatable robustness
- High DC stability
- High short-circuit capability

Mechanical Features

- IHM B housing
- Package with CTI > 600
- AlSiC base plate for increased thermal cycling capability
- Isolated base plate

Module Label Code

Barcode Code 128



DMX - Code



Content of the Code

Content of the Code	Digit
Module Serial Number	1 - 5
Module Material Number	6 - 11
Production Order Number	12 - 19
Datecode (Production Year)	20 - 21
Datecode (Production Week)	22 - 23

IGBT, 逆变器 / IGBT, Inverter

最大额定值 / Maximum Rated Values

集电极 - 发射极电压 Collector-emitter voltage	$T_{vj} = -40^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	V_{CES}	3300 3300	V
连续集电极直流电流 Continuous DC collector current	$T_C = 95^{\circ}\text{C}, T_{vj\max} = 150^{\circ}\text{C}$	I_{CDC}	1000	A
集电极重复峰值电流 Repetitive peak collector current	$t_P = 1\text{ ms}$	I_{CRM}	2000	A
栅极 - 发射极峰值电压 Gate-emitter peak voltage		V_{GES}	+/-20	V

特征值 / Characteristic Values

			min.	typ.	max.	
集电极 - 发射极饱和电压 Collector-emitter saturation voltage	$I_C = 1000\text{ A}$ $V_{GE} = 15\text{ V}$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	$V_{CE\text{ sat}}$	2,55 3,00 3,15	3,10 3,45	V V V
栅极阈值电压 Gate threshold voltage	$I_C = 48,0\text{ mA}, V_{CE} = V_{GE}, T_{vj} = 25^{\circ}\text{C}$		V_{GEth}	5,20	5,80 6,40	V
栅极电荷 Gate charge	$V_{GE} = -15 / 15\text{ V}, V_{CE} = 1800\text{ V}$		Q_G	28,0		μC
内部栅极电阻 Internal gate resistor	$T_{vj} = 25^{\circ}\text{C}$		R_{Gint}	0,63		Ω
输入电容 Input capacitance	$f = 1000\text{ kHz}, T_{vj} = 25^{\circ}\text{C}, V_{CE} = 25\text{ V}, V_{GE} = 0\text{ V}$		C_{ies}	190		nF
反向传输电容 Reverse transfer capacitance	$f = 1000\text{ kHz}, T_{vj} = 25^{\circ}\text{C}, V_{CE} = 25\text{ V}, V_{GE} = 0\text{ V}$		C_{res}	4,00		nF
集电极-发射极截止电流 Collector-emitter cut-off current	$V_{CE} = 3300\text{ V}, V_{GE} = 0\text{ V}, T_{vj} = 25^{\circ}\text{C}$		I_{CES}		5,0	mA
栅极-发射极漏电流 Gate-emitter leakage current	$V_{CE} = 0\text{ V}, V_{GE} = 20\text{ V}, T_{vj} = 25^{\circ}\text{C}$		I_{GES}		400	nA
开通延迟时间(电感负载) Turn-on delay time, inductive load	$I_C = 1000\text{ A}, V_{CE} = 1800\text{ V}$ $V_{GE} = -15 / 15\text{ V}$ $R_{Gon} = 0,71\ \Omega, C_{GE} = 220\text{ nF}$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	t_{don}	0,35 0,38 0,38		μs μs μs
上升时间(电感负载) Rise time, inductive load	$I_C = 1000\text{ A}, V_{CE} = 1800\text{ V}$ $V_{GE} = -15 / 15\text{ V}$ $R_{Gon} = 0,71\ \Omega, C_{GE} = 220\text{ nF}$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	t_r	0,35 0,38 0,38		μs μs μs
关断延迟时间(电感负载) Turn-off delay time, inductive load	$I_C = 1000\text{ A}, V_{CE} = 1800\text{ V}$ $V_{GE} = -15 / 15\text{ V}$ $R_{Goff} = 2,3\ \Omega, C_{GE} = 220\text{ nF}$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	t_{doff}	3,00 3,20 3,20		μs μs μs
下降时间(电感负载) Fall time, inductive load	$I_C = 1000\text{ A}, V_{CE} = 1800\text{ V}$ $V_{GE} = -15 / 15\text{ V}$ $R_{Goff} = 2,3\ \Omega, C_{GE} = 220\text{ nF}$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	t_f	0,30 0,35 0,35		μs μs μs
开通损耗能量(每脉冲) Turn-on energy loss per pulse	$I_C = 1000\text{ A}, V_{CE} = 1800\text{ V}, L_{\sigma} = 85\text{ nH}$ $di/dt = 3000\text{ A}/\mu\text{s} (T_{vj} = 150^{\circ}\text{C})$ $V_{GE} = -15 / 15\text{ V}, R_{Gon} = 0,71\ \Omega$ $C_{GE} = 220\text{ nF}$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	E_{on}	1250 1700 1950		mJ mJ mJ
关断损耗能量(每脉冲) Turn-off energy loss per pulse	$I_C = 1000\text{ A}, V_{CE} = 1800\text{ V}, L_{\sigma} = 85\text{ nH}$ $du/dt = 2100\text{ V}/\mu\text{s} (T_{vj} = 150^{\circ}\text{C})$ $V_{GE} = -15 / 15\text{ V}, R_{Goff} = 2,3\ \Omega$ $C_{GE} = 220\text{ nF}$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	E_{off}	1050 1400 1550		mJ mJ mJ
短路数据 SC data	$V_{GE} \leq 15\text{ V}, V_{CC} = 2500\text{ V}$ $V_{CEmax} = V_{CES} - L_{sCE} \cdot di/dt$ $t_P \leq 10\ \mu\text{s}, T_{vj} = 150^{\circ}\text{C}$		I_{SC}	4200		A
结 - 外壳热阻 Thermal resistance, junction to case	每个 IGBT / per IGBT		R_{thJC}		11,1	K/kW
外壳 - 散热器热阻 Thermal resistance, case to heatsink	每个 IGBT / per IGBT $\lambda_{Paste} = 1\text{ W}/(\text{m} \cdot \text{K}) / \lambda_{grease} = 1\text{ W}/(\text{m} \cdot \text{K})$		R_{thCH}	14,5		K/kW
在开关状态下温度 Temperature under switching conditions			$T_{vj\text{ op}}$	-40	150	$^{\circ}\text{C}$

二极管, 逆变器 / Diode, Inverter

最大额定值 / Maximum Rated Values

反向重复峰值电压 Repetitive peak reverse voltage	$T_{vj} = -40^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	V_{RRM}	3300 3300	V
连续正向直流电流 Continuous DC forward current		I_F	1000	A
正向重复峰值电流 Repetitive peak forward current	$t_P = 1 \text{ ms}$	I_{FRM}	2000	A
I^2t -值 I^2t - value	$V_R = 0 \text{ V}, t_P = 10 \text{ ms}, T_{vj} = 125^{\circ}\text{C}$ $V_R = 0 \text{ V}, t_P = 10 \text{ ms}, T_{vj} = 150^{\circ}\text{C}$	I^2t	260 245	kA^2s kA^2s
最大损耗功率 Maximum power dissipation	$T_{vj} = 150^{\circ}\text{C}$	P_{RQM}	1600	kW
最小开通时间 Minimum turn-on time		$t_{on \text{ min}}$	10,0	μs

特征值 / Characteristic Values

			min.	typ.	max.	
正向电压 Forward voltage	$I_F = 1000 \text{ A}, V_{GE} = 0 \text{ V}$ $I_F = 1000 \text{ A}, V_{GE} = 0 \text{ V}$ $I_F = 1000 \text{ A}, V_{GE} = 0 \text{ V}$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	V_F		3,10 2,75 2,65	3,85 3,25 V V V
反向恢复峰值电流 Peak reverse recovery current	$I_F = 1000 \text{ A}, -di_F/dt = 3000 \text{ A}/\mu\text{s} (T_{vj}=150^{\circ}\text{C})$ $V_R = 1800 \text{ V}$ $V_{GE} = -15 \text{ V}$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	I_{RM}		1000 1200 1250	A A A
恢复电荷 Recovered charge	$I_F = 1000 \text{ A}, -di_F/dt = 3000 \text{ A}/\mu\text{s} (T_{vj}=150^{\circ}\text{C})$ $V_R = 1800 \text{ V}$ $V_{GE} = -15 \text{ V}$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	Q_r		450 900 1050	μC μC μC
反向恢复损耗 (每脉冲) Reverse recovery energy	$I_F = 1000 \text{ A}, -di_F/dt = 3000 \text{ A}/\mu\text{s} (T_{vj}=150^{\circ}\text{C})$ $V_R = 1800 \text{ V}$ $V_{GE} = -15 \text{ V}$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	E_{rec}		450 1100 1300	mJ mJ mJ
结 - 外壳热阻 Thermal resistance, junction to case	每个二极管 / per diode		R_{thJC}			19,8 K/kW
外壳 - 散热器热阻 Thermal resistance, case to heatsink	每个二极管 / per diode $\lambda_{\text{Paste}} = 1 \text{ W}/(\text{m}\cdot\text{K})$ / $\lambda_{\text{grease}} = 1 \text{ W}/(\text{m}\cdot\text{K})$		R_{thCH}		16,5	K/kW
在开关状态下温度 Temperature under switching conditions			$T_{vj \text{ op}}$	-40		150 $^{\circ}\text{C}$

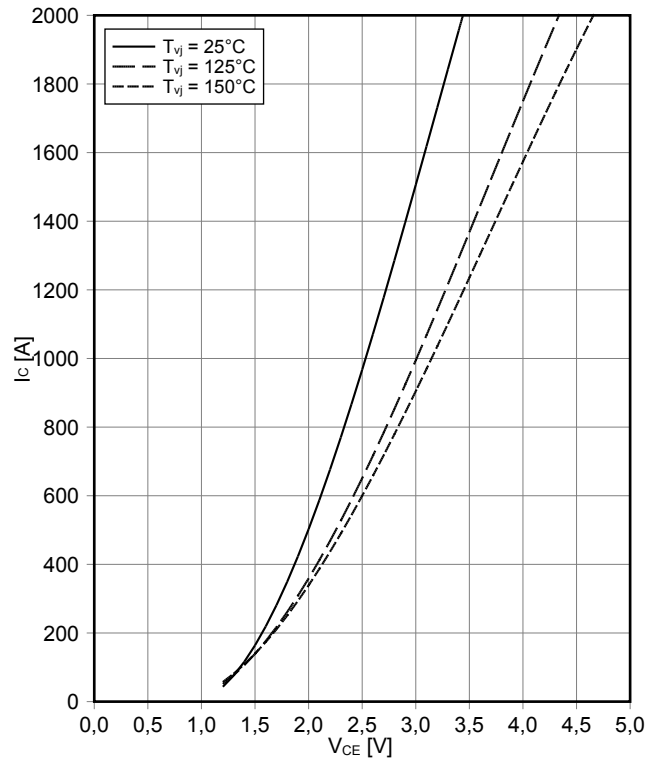
模块 / Module

绝缘测试电压 Isolation test voltage	RMS, $f = 50 \text{ Hz}$, $t = 1 \text{ min.}$	V_{ISOL}	6,0	kV
局部放电停止电压 Partial discharge extinction voltage	RMS, $f = 50 \text{ Hz}$, $Q_{\text{PD}} \leq 10 \text{ pC}$	V_{ISOL}	2,6	kV
DC 稳定性 DC stability	$T_{\text{vj}} = 25^\circ\text{C}$, 100 fit	$V_{\text{CE D}}$	2100	V
模块基板材料 Material of module baseplate			AlSiC	
爬电距离 Creepage distance	端子至散热器 / terminal to heatsink 端子至端子 / terminal to terminal		32,2	mm
电气间隙 Clearance	端子至散热器 / terminal to heatsink 端子至端子 / terminal to terminal		19,1	mm
相对电痕指数 Comperative tracking index		CTI	> 600	
min. typ. max.				
杂散电感,模块 Stray inductance module		L_{sCE}	9,0	nH
模块引线电阻,端子-芯片 Module lead resistance, terminals - chip	$T_{\text{c}} = 25^\circ\text{C}$, 每个开关 / per switch	$R_{\text{CC}'+\text{EE}'}$	0,19	m Ω
储存温度 Storage temperature		T_{stg}	-40	150 °C
模块安装的安装扭矩 Mounting torque for modul mounting	螺丝 M6 根据相应的应用手册进行安装 Screw M6 - Mounting according to valid application note	M	4,25	5,75 Nm
端子联接扭矩 Terminal connection torque	螺丝 M4 根据相应的应用手册进行安装 Screw M4 - Mounting according to valid application note	M	1,8	- 2,1 Nm
	螺丝 M8 根据相应的应用手册进行安装 Screw M8 - Mounting according to valid application note		8,0	- 10 Nm
重量 Weight		G	800	g

输出特性 IGBT, 逆变器 (典型)

output characteristic IGBT, Inverter (typical)

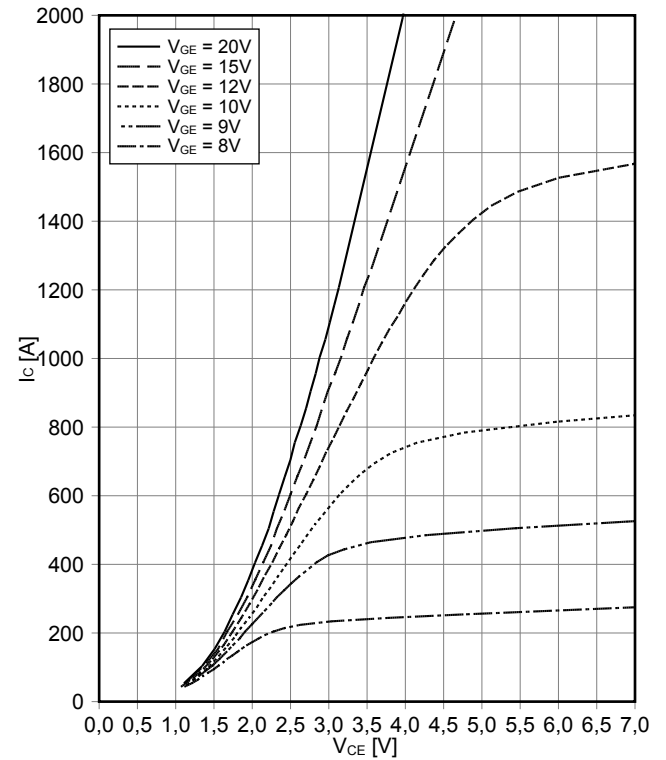
$I_C = f(V_{CE})$
 $V_{GE} = 15\text{ V}$



输出特性 IGBT, 逆变器 (典型)

output characteristic IGBT, Inverter (typical)

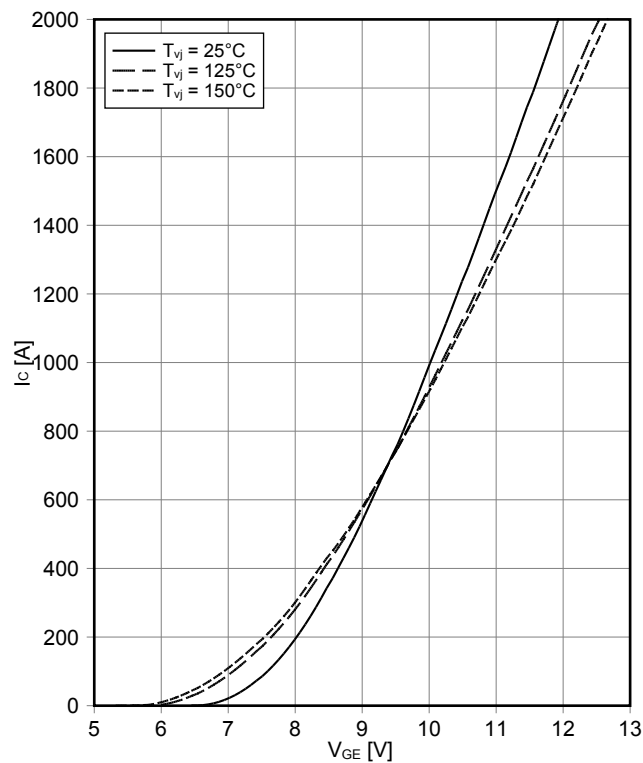
$I_C = f(V_{CE})$
 $T_{vj} = 150^\circ\text{C}$



传输特性 IGBT, 逆变器 (典型)

transfer characteristic IGBT, Inverter (typical)

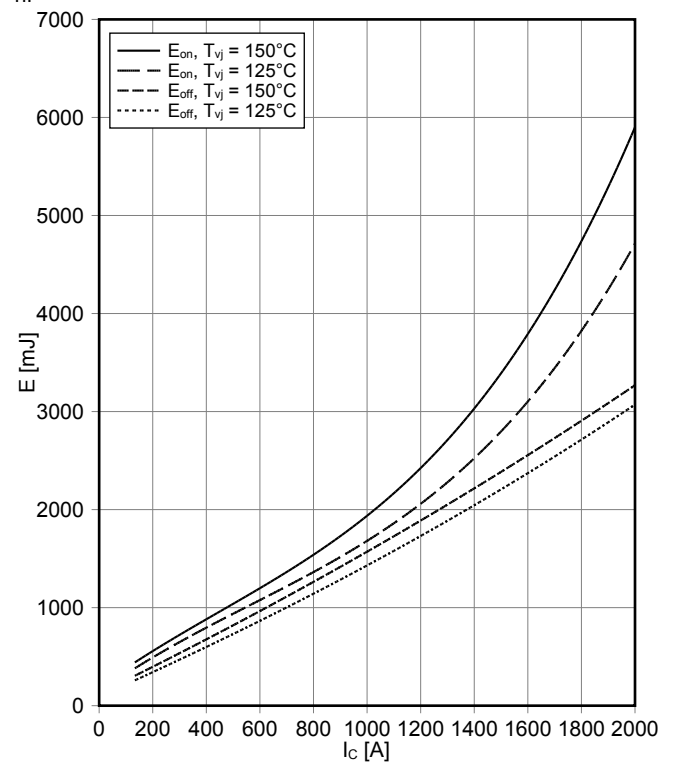
$I_C = f(V_{GE})$
 $V_{CE} = 20\text{ V}$



开关损耗 IGBT, 逆变器 (典型)

switching losses IGBT, Inverter (typical)

$E_{on} = f(I_C)$, $E_{off} = f(I_C)$
 $V_{GE} = \pm 15\text{ V}$, $R_{Gon} = 0.71\ \Omega$, $R_{Goff} = 2.3\ \Omega$, $V_{CE} = 1800\text{ V}$, $C_{GE} = 220\text{ nF}$

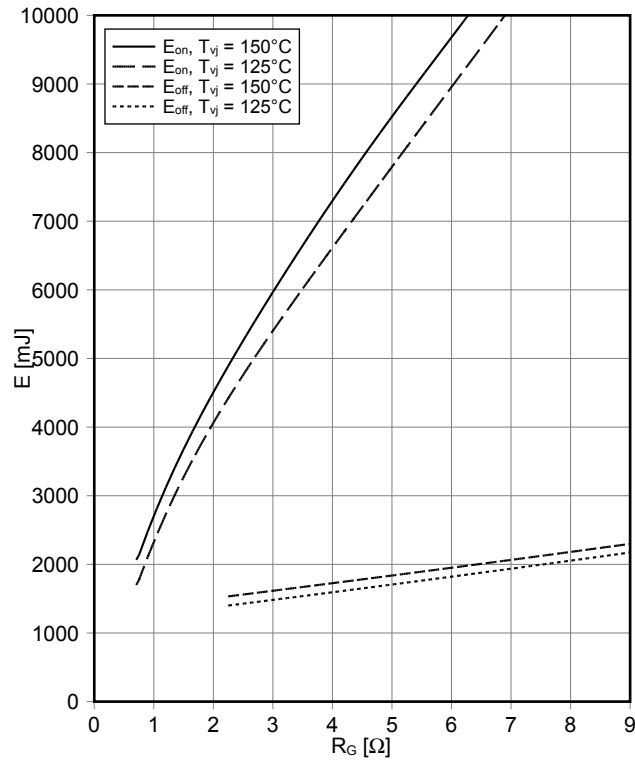


开关损耗 IGBT, 逆变器 (典型)

switching losses IGBT, Inverter (typical)

$E_{on} = f(R_G)$, $E_{off} = f(R_G)$

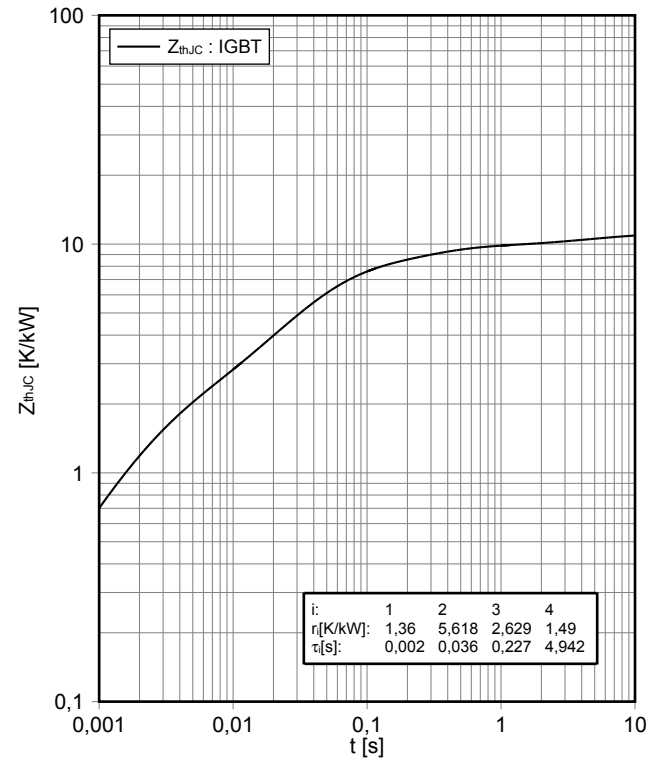
$V_{GE} = \pm 15 \text{ V}$, $I_C = 1000 \text{ A}$, $V_{CE} = 1800 \text{ V}$, $C_{GE} = 220 \text{ nF}$



瞬态热阻抗 IGBT, 逆变器

transient thermal impedance IGBT, Inverter

$Z_{thJC} = f(t)$

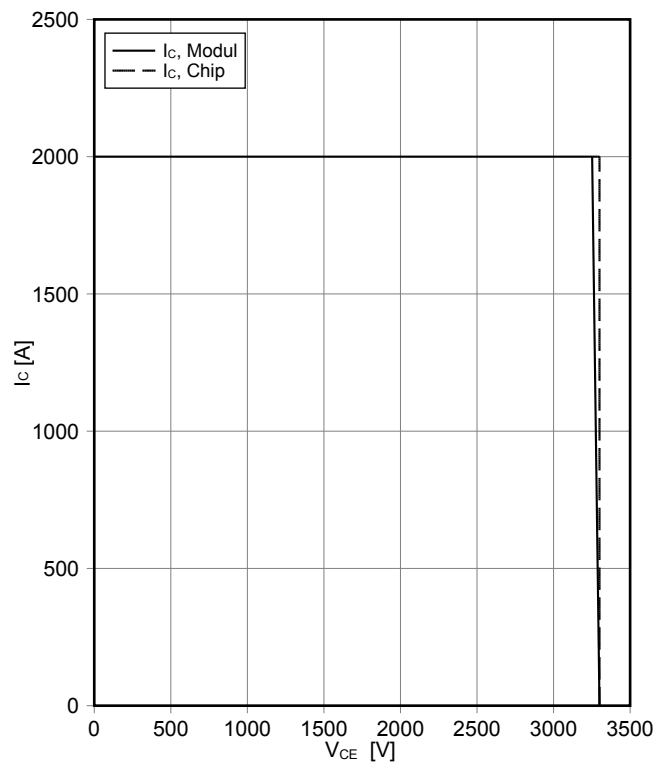


反偏安全工作区 IGBT, 逆变器 (RBSOA)

reverse bias safe operating area IGBT, Inverter (RBSOA)

$I_C = f(V_{CE})$

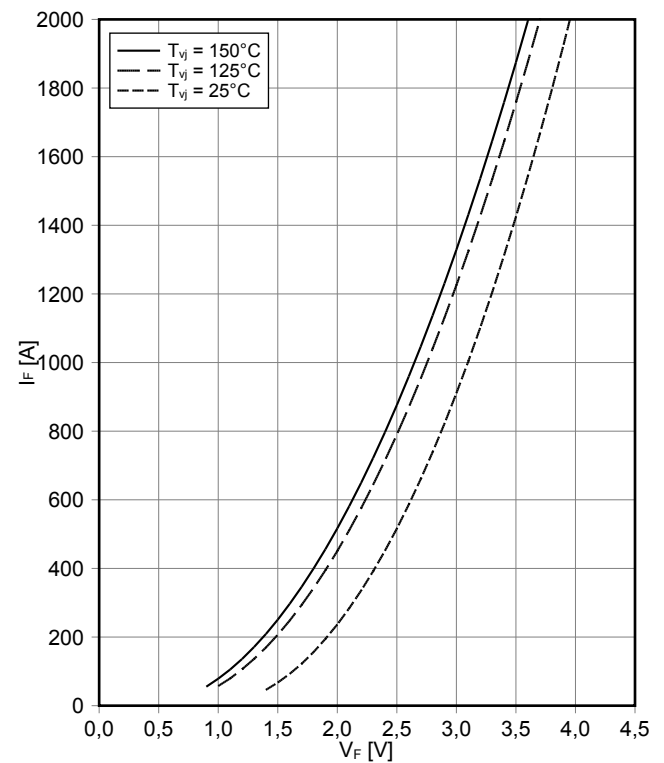
$V_{GE} = \pm 15 \text{ V}$, $R_{Goff} = 2.3 \Omega$, $T_{vj} = 150^\circ\text{C}$, $C_{GE} = 220 \text{ nF}$



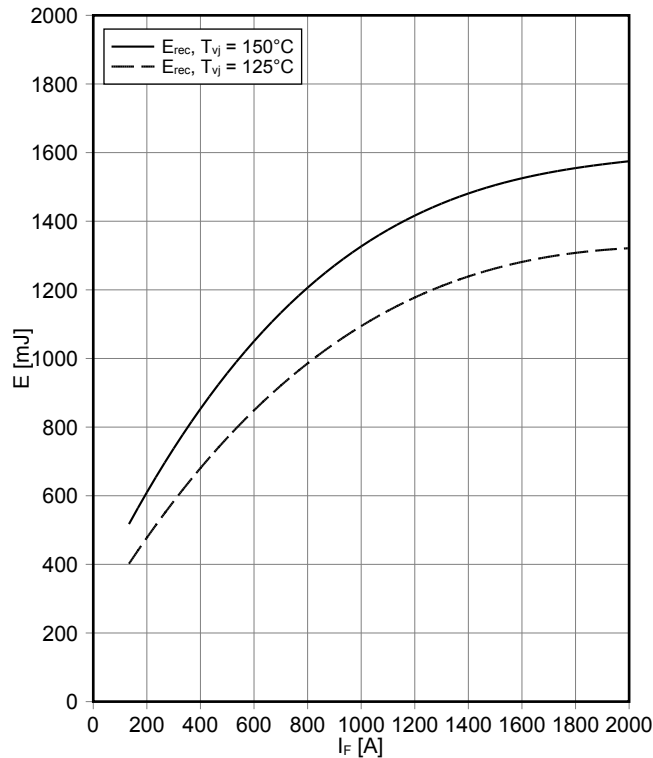
正向偏压特性 二极管, 逆变器 (典型)

forward characteristic of Diode, Inverter (typical)

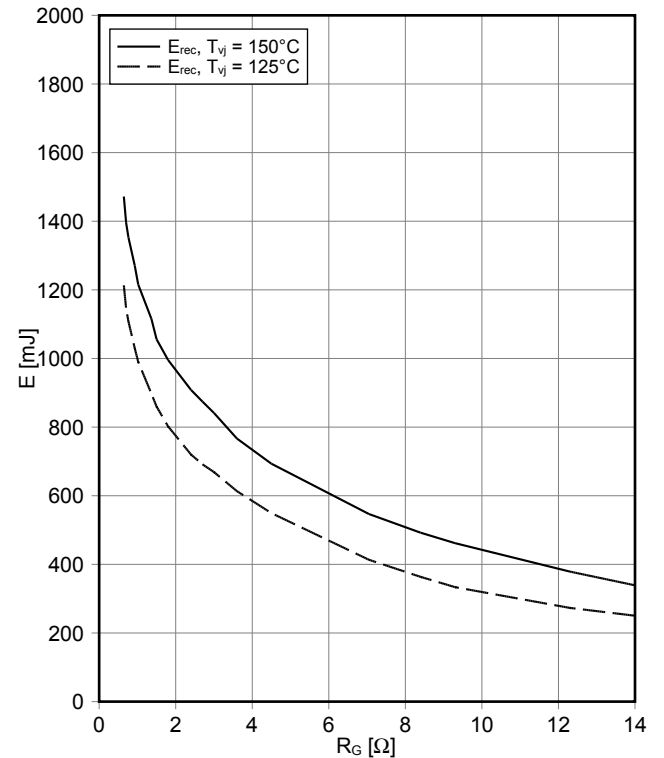
$I_F = f(V_F)$



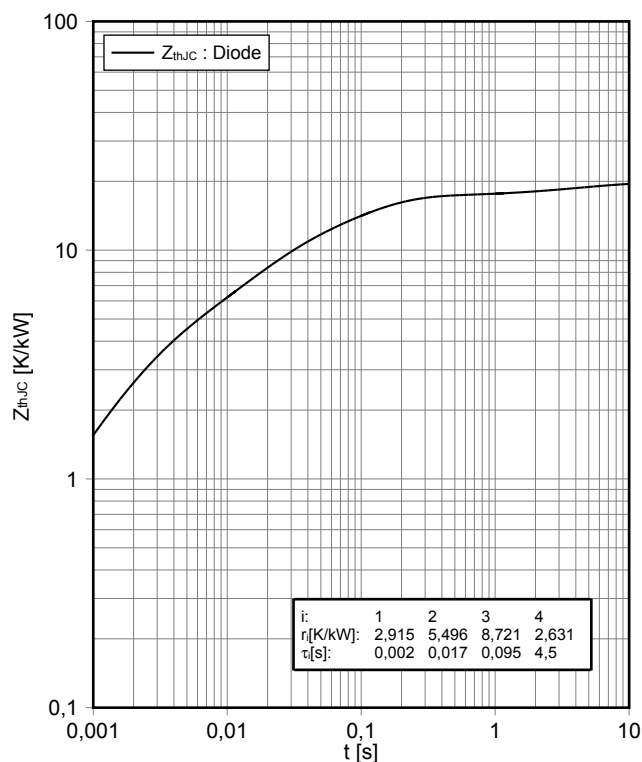
开关损耗 二极管,逆变器 (典型)
switching losses Diode, Inverter (typical)
 $E_{rec} = f(I_F)$
 $R_{Gon} = 0.71 \Omega$, $V_{CE} = 1800 \text{ V}$



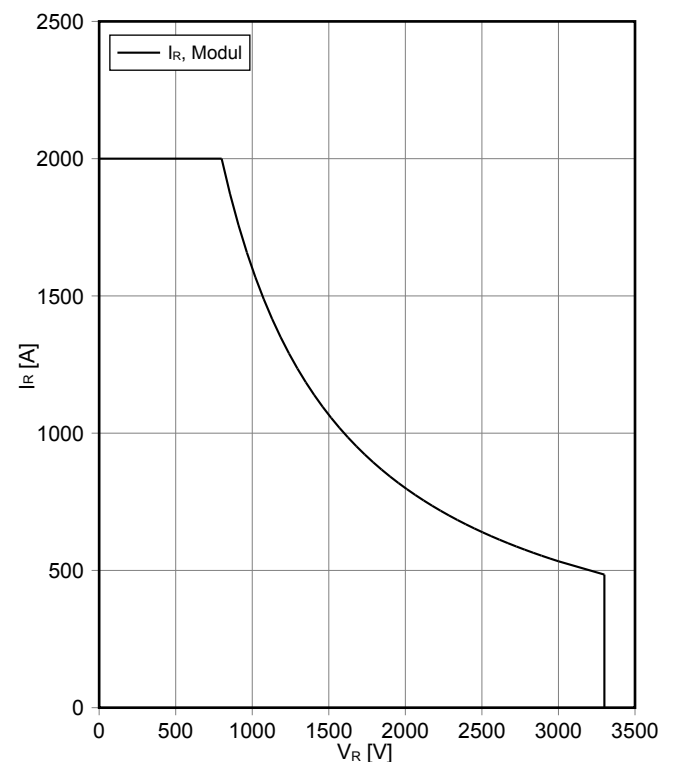
开关损耗 二极管,逆变器 (典型)
switching losses Diode, Inverter (typical)
 $E_{rec} = f(R_G)$
 $I_F = 1000 \text{ A}$, $V_{CE} = 1800 \text{ V}$



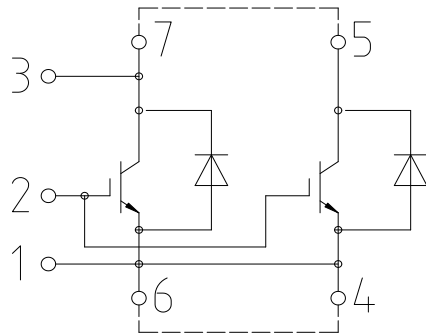
瞬态热阻抗 二极管,逆变器
transient thermal impedance Diode, Inverter
 $Z_{thJC} = f(t)$



安全工作区 二极管,逆变器 (SOA)
safe operation area Diode, Inverter (SOA)
 $I_R = f(V_R)$
 $T_{vj} = 150^\circ\text{C}$

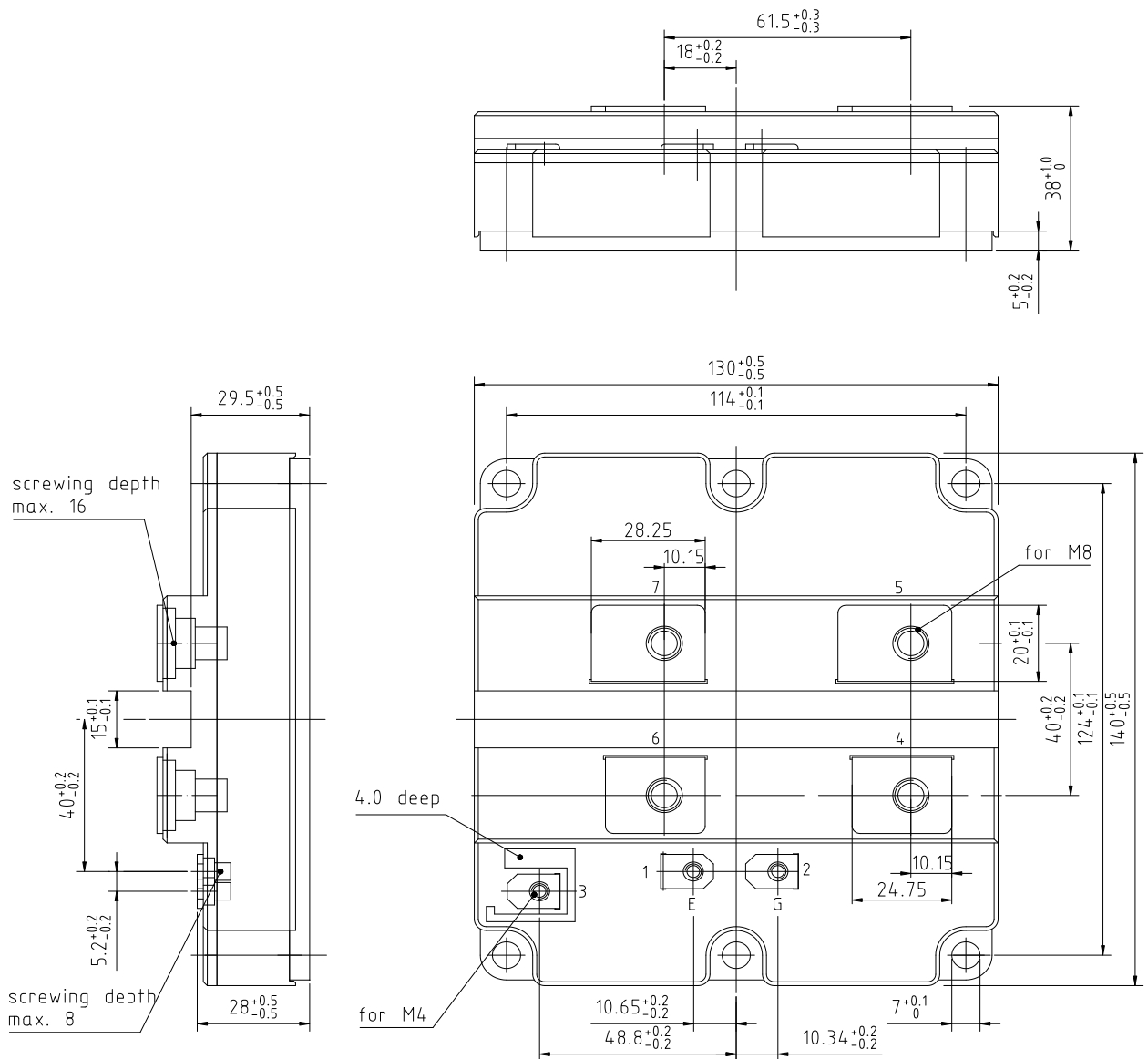


接线图 / Circuit diagram



external connection
(to be done)

封装尺寸 / Package outlines



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